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Understanding Embedded - FPGAs (Field Programmable Gate Array)

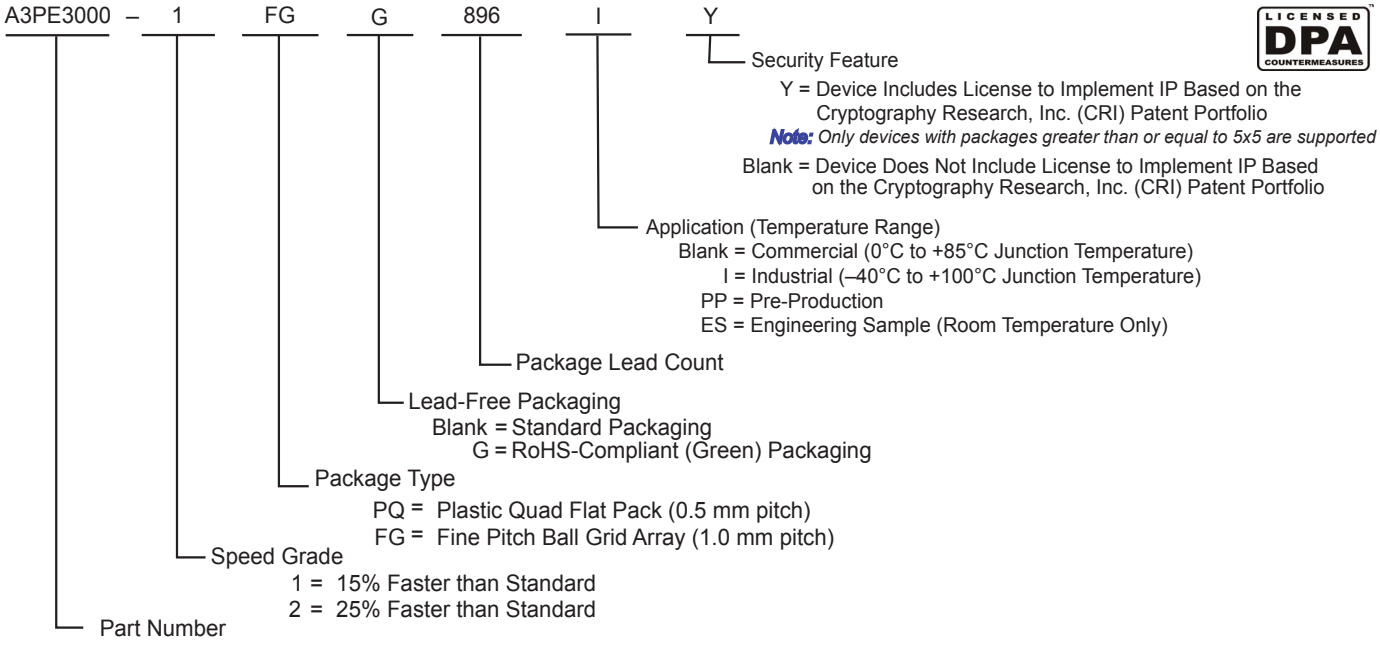
Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details	
Product Status	Active
Number of LABs/CLBs	-
Number of Logic Elements/Cells	-
Total RAM Bits	516096
Number of I/O	147
Number of Gates	3000000
Voltage - Supply	1.425V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	208-BFQFP
Supplier Device Package	208-PQFP (28x28)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/m1a3pe3000-2pqg208i

ProASIC3E Ordering Information



ProASIC3E Devices

A3PE600 = 600,000 System Gates
A3PE1500 = 1,500,000 System Gates
A3PE3000 = 3,000,000 System Gates

ProASIC3E Devices with Cortex-M1

M1A3PE1500 = 1,500,000 System Gates
M1A3PE3000 = 3,000,000 System Gates

Single Chip

Flash-based FPGAs store their configuration information in on-chip flash cells. Once programmed, the configuration data is an inherent part of the FPGA structure, and no external configuration data needs to be loaded at system power-up (unlike SRAM-based FPGAs). Therefore, flash-based ProASIC3E FPGAs do not require system configuration components such as EEPROMs or microcontrollers to load device configuration data. This reduces bill-of-materials costs and PCB area, and increases security and system reliability.

Instant On

Flash-based ProASIC3E devices support Level 0 of the Instant On classification standard. This feature helps in system component initialization, execution of critical tasks before the processor wakes up, setup and configuration of memory blocks, clock generation, and bus activity management. The Instant On feature of flash-based ProASIC3E devices greatly simplifies total system design and reduces total system cost, often eliminating the need for CPLDs and clock generation PLLs that are used for these purposes in a system. In addition, glitches and brownouts in system power will not corrupt the ProASIC3E device's flash configuration, and unlike SRAM-based FPGAs, the device will not have to be reloaded when system power is restored. This enables the reduction or complete removal of the configuration PROM, expensive voltage monitor, brownout detection, and clock generator devices from the PCB design. Flash-based ProASIC3E devices simplify total system design and reduce cost and design risk while increasing system reliability and improving system initialization time.

Firm Errors

Firm errors occur most commonly when high-energy neutrons, generated in the upper atmosphere, strike a configuration cell of an SRAM FPGA. The energy of the collision can change the state of the configuration cell and thus change the logic, routing, or I/O behavior in an unpredictable way. These errors are impossible to prevent in SRAM FPGAs. The consequence of this type of error can be a complete system failure. Firm errors do not exist in the configuration memory of ProASIC3E flash-based FPGAs. Once it is programmed, the flash cell configuration element of ProASIC3E FPGAs cannot be altered by high-energy neutrons and is therefore immune to them. Recoverable (or soft) errors occur in the user data SRAM of all FPGA devices. These can easily be mitigated by using error detection and correction (EDAC) circuitry built into the FPGA fabric.

Low Power

Flash-based ProASIC3E devices exhibit power characteristics similar to an ASIC, making them an ideal choice for power-sensitive applications. ProASIC3E devices have only a very limited power-on current surge and no high-current transition period, both of which occur on many FPGAs.

ProASIC3E devices also have low dynamic power consumption to further maximize power savings.

Advanced Flash Technology

The ProASIC3E family offers many benefits, including nonvolatility and reprogrammability through an advanced flash-based, 130-nm LVCMOS process with seven layers of metal. Standard CMOS design techniques are used to implement logic and control functions. The combination of fine granularity, enhanced flexible routing resources, and abundant flash switches allows for very high logic utilization without compromising device routability or performance. Logic functions within the device are interconnected through a four-level routing hierarchy.

Pro I/Os with Advanced I/O Standards

The ProASIC3E family of FPGAs features a flexible I/O structure, supporting a range of voltages (1.5 V, 1.8 V, 2.5 V, and 3.3 V). ProASIC3E FPGAs support 19 different I/O standards, including single-ended, differential, and voltage-referenced. The I/Os are organized into banks, with eight banks per device (two per side). The configuration of these banks determines the I/O standards supported. Each I/O bank is subdivided into VREF minibanks, which are used by voltage-referenced I/Os. VREF minibanks contain 8 to 18 I/Os. All the I/Os in a given minibank share a common VREF line. Therefore, if any I/O in a given VREF minibank is configured as a VREF pin, the remaining I/Os in that minibank will be able to use that reference voltage.

Each I/O module contains several input, output, and enable registers. These registers allow the implementation of the following:

- Single-Data-Rate applications (e.g., PCI 66 MHz, bidirectional SSTL 2 and 3, Class I and II)
- Double-Data-Rate applications (e.g., DDR LVDS, B-LVDS, and M-LVDS I/Os for point-to-point communications, and DDR 200 MHz SRAM using bidirectional HSTL Class II)

ProASIC3E banks support M-LVDS with 20 multi-drop points.

Hot-swap (also called hot-plug, or hot-insertion) is the operation of hot-insertion or hot-removal of a card in a powered-up system.

Cold-sparing (also called cold-swap) refers to the ability of a device to leave system data undisturbed when the system is powered up, while the component itself is powered down, or when power supplies are floating.

Specifying I/O States During Programming

You can modify the I/O states during programming in FlashPro. In FlashPro, this feature is supported for PDB files generated from Designer v8.5 or greater. See the *FlashPro User's Guide* for more information.

Note: PDB files generated from Designer v8.1 to Designer v8.4 (including all service packs) have limited display of Pin Numbers only.

1. Load a PDB from the FlashPro GUI. You must have a PDB loaded to modify the I/O states during programming.
2. From the FlashPro GUI, click PDB Configuration. A FlashPoint – Programming File Generator window appears.
3. Click the Specify I/O States During Programming button to display the Specify I/O States During Programming dialog box.
4. Sort the pins as desired by clicking any of the column headers to sort the entries by that header. Select the I/Os you wish to modify (Figure 1-3 on page 1-7).
5. Set the I/O Output State. You can set Basic I/O settings if you want to use the default I/O settings for your pins, or use Custom I/O settings to customize the settings for each pin. Basic I/O state settings:

   1 – I/O is set to drive out logic High

   0 – I/O is set to drive out logic Low

   Last Known State – I/O is set to the last value that was driven out prior to entering the programming mode, and then held at that value during programming

   Z -Tri-State: I/O is tristated

Power Calculation Methodology

This section describes a simplified method to estimate power consumption of an application. For more accurate and detailed power estimations, use the SmartPower tool in the Libero SoC software.

The power calculation methodology described below uses the following variables:

- The number of PLLs as well as the number and the frequency of each output clock generated
- The number of combinatorial and sequential cells used in the design
- The internal clock frequencies
- The number and the standard of I/O pins used in the design
- The number of RAM blocks used in the design
- Toggle rates of I/O pins as well as VersaTiles—guidelines are provided in Table 2-11 on page 2-11.
- Enable rates of output buffers—guidelines are provided for typical applications in Table 2-12 on page 2-11.
- Read rate and write rate to the memory—guidelines are provided for typical applications in Table 2-12 on page 2-11. The calculation should be repeated for each clock domain defined in the design.

Methodology

Total Power Consumption—P_{TOTAL}

$P_{TOTAL} = P_{STAT} + P_{DYN}$

P_{STAT} is the total static power consumption.

P_{DYN} is the total dynamic power consumption.

Total Static Power Consumption—P_{STAT}

$P_{STAT} = PDC1 + N_{INPUTS} * PDC2 + N_{OUTPUTS} * PDC3$

N_{INPUTS} is the number of I/O input buffers used in the design.

$N_{OUTPUTS}$ is the number of I/O output buffers used in the design.

Total Dynamic Power Consumption—P_{DYN}

$P_{DYN} = P_{CLOCK} + P_{S\text{-}CELL} + P_{C\text{-}CELL} + P_{NET} + P_{INPUTS} + P_{OUTPUTS} + P_{MEMORY} + P_{PLL}$

Global Clock Contribution—P_{CLOCK}

$P_{CLOCK} = (PAC1 + N_{SPINE} * PAC2 + N_{ROW} * PAC3 + N_{S\text{-}CELL} * PAC4) * F_{CLK}$

N_{SPINE} is the number of global spines used in the user design—guidelines are provided in the "Spine Architecture" section of the Global Resources chapter in the *ProASIC3E FPGA Fabric User's Guide*.

N_{ROW} is the number of VersaTile rows used in the design—guidelines are provided in the "Spine Architecture" section of the Global Resources chapter in the *ProASIC3E FPGA Fabric User's Guide*.

F_{CLK} is the global clock signal frequency.

$N_{S\text{-}CELL}$ is the number of VersaTiles used as sequential modules in the design.

PAC1, PAC2, PAC3, and PAC4 are device-dependent.

Sequential Cells Contribution—$P_{S\text{-}CELL}$

$P_{S\text{-}CELL} = N_{S\text{-}CELL} * (PAC5 + \alpha_1 / 2 * PAC6) * F_{CLK}$

$N_{S\text{-}CELL}$ is the number of VersaTiles used as sequential modules in the design. When a multi-tile sequential cell is used, it should be accounted for as 1.

α_1 is the toggle rate of VersaTile outputs—guidelines are provided in Table 2-11 on page 2-11.

F_{CLK} is the global clock signal frequency.

Timing Characteristics

Table 2-27 • 3.3 V LVTTL / 3.3 V LVCMOS High Slew
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 3.0 V

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{PYS}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	Std.	0.66	7.88	0.04	1.20	1.57	0.43	8.03	6.70	2.69	2.59	10.26	8.94	ns
	–1	0.56	6.71	0.04	1.02	1.33	0.36	6.83	5.70	2.29	2.20	8.73	7.60	ns
	–2	0.49.	5.89	0.03	0.90	1.17	0.32	6.00	5.01	2.01	1.93	7.67	6.67	ns
4 mA	Std.	0.66	7.88	0.04	1.20	1.57	0.43	8.03	6.70	2.69	2.59	10.26	8.94	ns
	–1	0.56	6.71	0.04	1.02	1.33	0.36	6.83	5.70	2.29	2.20	8.73	7.60	ns
	–2	0.49	5.89	0.03	0.90	1.17	0.32	6.00	5.01	2.01	1.93	7.67	6.67	ns
6 mA	Std.	0.66	5.08	0.04	1.20	1.57	0.43	5.17	4.14	3.05	3.21	7.41	6.38	ns
	–1	0.56	4.32	0.04	1.02	1.33	0.36	4.40	3.52	2.59	2.73	6.30	5.43	ns
	–2	0.49	3.79	0.03	0.90	1.17	0.32	3.86	3.09	2.28	2.40	5.53	4.76	ns
8 mA	Std.	0.66	5.08	0.04	1.20	1.57	0.43	5.17	4.14	3.05	3.21	7.41	6.38	ns
	–1	0.56	4.32	0.04	1.02	1.33	0.36	4.40	3.52	2.59	2.73	6.30	5.43	ns
	–2	0.49	3.79	0.03	0.90	1.17	0.32	3.86	3.09	2.28	2.40	5.53	4.76	ns
12 mA	Std.	0.66	3.67	0.04	1.20	1.57	0.43	3.74	2.87	3.28	3.61	5.97	5.11	ns
	–1	0.56	3.12	0.04	1.02	1.33	0.36	3.18	2.44	2.79	3.07	5.08	4.34	ns
	–2	0.49	2.74	0.03	0.90	1.17	0.32	2.79	2.14	2.45	2.70	4.46	3.81	ns
16 mA	Std.	0.66	3.46	0.04	1.20	1.57	0.43	3.53	2.61	3.33	3.72	5.76	4.84	ns
	–1	0.56	2.95	0.04	1.02	1.33	0.36	3.00	2.22	2.83	3.17	4.90	4.12	ns
	–2	0.49	2.59	0.03	0.90	1.17	0.32	2.63	1.95	2.49	2.78	4.30	3.62	ns
24 mA	Std.	0.66	3.21	0.04	1.20	1.57	0.43	3.27	2.16	3.39	4.13	5.50	4.39	ns
	–1	0.56	2.73	0.04	1.02	1.33	0.36	2.78	1.83	2.88	3.51	4.68	3.74	ns
	–2	0.49	2.39	0.03	0.90	1.17	0.32	2.44	1.61	2.53	3.08	4.11	3.28	ns

Notes:

1. *Software default selection highlighted in gray.*
2. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-5 for derating values.*

Table 2-28 • 3.3 V LVTTL / 3.3 V LVCMOS Low Slew
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 3.0 V

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{PYS}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	Std.	0.66	11.01	0.04	1.20	1.57	0.43	11.21	9.05	2.69	2.44	13.45	11.29	ns
	–1	0.56	9.36	0.04	1.02	1.33	0.36	9.54	7.70	2.29	2.08	11.44	9.60	ns
	–2	0.49	8.22	0.03	0.90	1.17	0.32	8.37	6.76	2.01	1.82	10.04	8.43	ns
4 mA	Std.	0.66	11.01	0.04	1.20	1.57	0.43	11.21	9.05	2.69	2.44	13.45	11.29	ns
	–1	0.56	9.36	0.04	1.02	1.33	0.36	9.54	7.70	2.29	2.08	11.44	9.60	ns
	–2	0.49	8.22	0.03	0.90	1.17	0.32	8.37	6.76	2.01	1.82	10.04	8.43	ns
6 mA	Std.	0.66	7.86	0.04	1.20	1.57	0.43	8.01	6.44	3.04	3.06	10.24	8.68	ns
	–1	0.56	6.69	0.04	1.02	1.33	0.36	6.81	5.48	2.58	2.61	8.71	7.38	ns
	–2	0.49	5.87	0.03	0.90	1.17	0.32	5.98	4.81	2.27	2.29	7.65	6.48	ns
8 mA	Std.	0.66	7.86	0.04	1.20	1.57	0.43	8.01	6.44	3.04	3.06	10.24	8.68	ns
	–1	0.56	6.69	0.04	1.02	1.33	0.36	6.81	5.48	2.58	2.61	8.71	7.38	ns
	–2	0.49	5.87	0.03	0.90	1.17	0.32	5.98	4.81	2.27	2.29	7.65	6.48	ns

2.5 V GTL

Gunning Transceiver Logic is a high-speed bus standard (JESD8-3). It provides a differential amplifier input buffer and an open-drain output buffer. The VCCI pin should be connected to 2.5 V.

Table 2-51 • Minimum and Maximum DC Input and Output Levels

2.5 GTL	VIL		VIH		VOL	VOH	IOL	IOH	IOSL	IOSH	IIL	IIH
Drive Strength	Min., V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA	Max. mA[1]	Max. mA[1]	µA[2]	µA[2]
20 mA[3]	–0.3	VREF – 0.05	VREF + 0.05	3.6	0.4	–	20	20	124	169	10	10

Notes:

1. *Currents are measured at high temperature (100°C junction temperature) and maximum voltage.*
2. *Currents are measured at 85°C junction temperature.*
3. *Output drive strength is below JEDEC specification.*

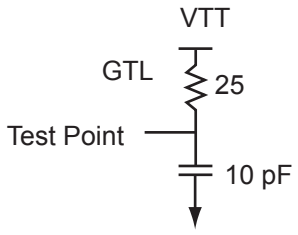


Figure 2-13 • AC Loading

Table 2-52 • AC Waveforms, Measuring Points, and Capacitive Loads

Input Low (V)	Input High (V)	Measuring Point* (V)	VREF (typ.) (V)	VTT (typ.) (V)	C_{LOAD} (pF)
VREF – 0.05	VREF + 0.05	0.8	0.8	1.2	10

*Note: *Measuring point = Vtrip. See Table 2-15 on page 2-18 for a complete table of trip points.*

Timing Characteristics

Table 2-53 • 2.5 V GTL
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 3.0 V VREF = 0.8 V

Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
Std.	0.60	2.13	0.04	2.46	0.43	2.16	2.13			4.40	4.36	ns
–1	0.51	1.81	0.04	2.09	0.36	1.84	1.81			3.74	3.71	ns
–2	0.45	1.59	0.03	1.83	0.32	1.61	1.59			3.28	3.26	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-5 for derating values.

2.5 V GTL+

Gunning Transceiver Logic Plus is a high-speed bus standard (JESD8-3). It provides a differential amplifier input buffer and an open-drain output buffer. The VCCI pin should be connected to 2.5 V.

Table 2-57 • Minimum and Maximum DC Input and Output Levels

2.5 V GTL+	VIL		VIH		VOL	VOH	IOL	IOH	IOSL	IOSH	IIL	IIH
Drive Strength	Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA	Max. mA[1]	Max. mA[1]	µA[2]	µA[2]
33 mA	–0.3	VREF – 0.1	VREF + 0.1	3.6	0.6	–	33	33	124	169	10	10

Notes:

1. *Currents are measured at high temperature (100°C junction temperature) and maximum voltage.*
2. *Currents are measured at 85°C junction temperature.*

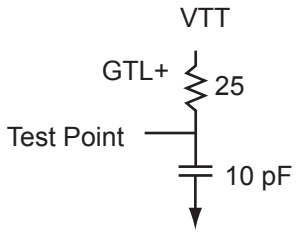


Figure 2-15 • AC Loading

Table 2-58 • AC Waveforms, Measuring Points, and Capacitive Loads

Input Low (V)	Input High (V)	Measuring Point* (V)	VREF (typ.) (V)	VTT (typ.) (V)	C_{LOAD} (pF)
VREF – 0.1	VREF + 0.1	1.0	1.0	1.5	10

*Note: *Measuring point = Vtrip. See Table 2-15 on page 2-18 for a complete table of trip points.*

Timing Characteristics

Table 2-59 • 2.5 V GTL+
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 2.3 V, VREF = 1.0 V

Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
Std.	0.60	2.21	0.04	1.51	0.43	2.25	2.10			4.48	4.34	ns
–1	0.51	1.88	0.04	1.29	0.36	1.91	1.79			3.81	3.69	ns
–2	0.45	1.65	0.03	1.13	0.32	1.68	1.57			3.35	3.24	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-5 for derating values.

SSTL3 Class I

Stub-Speed Terminated Logic for 3.3 V memory bus standard (JESD8-8). ProASIC3E devices support Class I. This provides a differential amplifier input buffer and a push-pull output buffer.

Table 2-72 • Minimum and Maximum DC Input and Output Levels

SSTL3 Class I	VIL		VIH		VOL	VOH	IOL	IOH	IOSL	IOSH	IIL	IIH
Drive Strength	Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA	Max. mA[1]	Max. mA[1]	µA[2]	µA[2]
14 mA	–0.3	VREF – 0.2	VREF + 0.2	3.6	0.7	VCCI – 1.1	14	14	54	51	10	10

Notes:

1. *Currents are measured at high temperature (100°C junction temperature) and maximum voltage.*
2. *Currents are measured at 85°C junction temperature.*

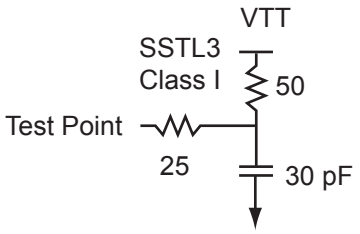


Figure 2-20 • AC Loading

Table 2-73 • AC Waveforms, Measuring Points, and Capacitive Loads

Input Low (V)	Input High (V)	Measuring Point* (V)	VREF (typ.) (V)	VTT (typ.) (V)	C_{LOAD} (pF)
VREF – 0.2	VREF + 0.2	1.5	1.5	1.485	30

*Note: *Measuring point = Vtrip. See Table 2-15 on page 2-18 for a complete table of trip points.*

Timing Characteristics

Table 2-74 • SSTL3 Class I
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 3.0 V, VREF = 1.5 V

Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
Std.	0.66	2.31	0.04	1.25	0.43	2.35	1.84			4.59	4.07	ns
–1	0.56	1.96	0.04	1.06	0.36	2.00	1.56			3.90	3.46	ns
–2	0.49	1.72	0.03	0.93	0.32	1.75	1.37			3.42	3.04	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-5 for derating values.

I/O Register Specifications

Fully Registered I/O Buffers with Synchronous Enable and Asynchronous Preset

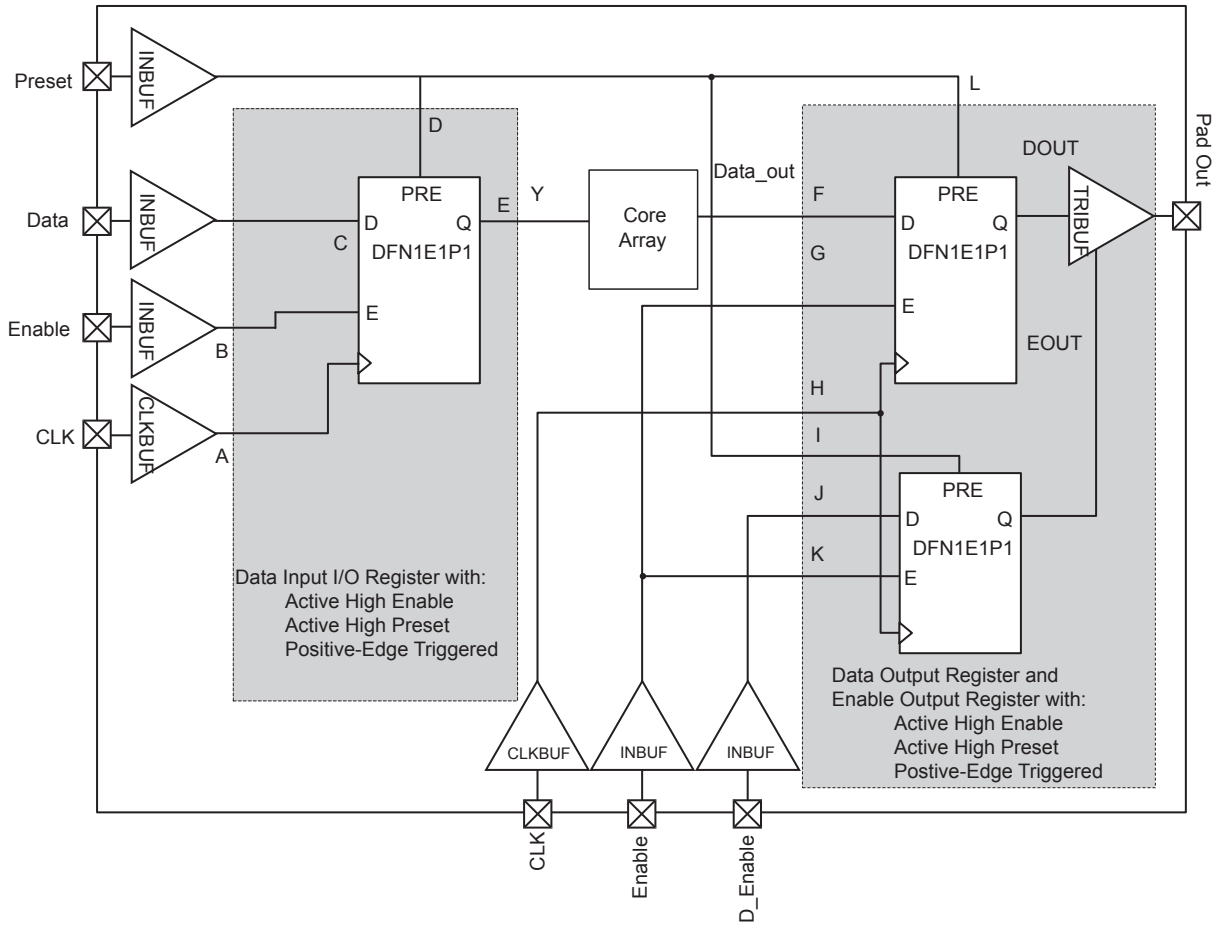


Figure 2-25 • **Timing Model of Registered I/O Buffers with Synchronous Enable and Asynchronous Preset**

***Table 2-84* • Parameter Definition and Measuring Nodes**

Parameter Name	Parameter Definition	Measuring Nodes (from, to)*
t_{OCLKQ}	Clock-to-Q of the Output Data Register	H, DOUT
t_{OSUD}	Data Setup Time for the Output Data Register	F, H
t_{OHD}	Data Hold Time for the Output Data Register	F, H
t_{OSUE}	Enable Setup Time for the Output Data Register	G, H
t_{OHE}	Enable Hold Time for the Output Data Register	G, H
t_{OPRE2Q}	Asynchronous Preset-to-Q of the Output Data Register	L, DOUT
$t_{OREMPRE}$	Asynchronous Preset Removal Time for the Output Data Register	L, H
$t_{ORECPRE}$	Asynchronous Preset Recovery Time for the Output Data Register	L, H
t_{OECLKQ}	Clock-to-Q of the Output Enable Register	H, EOUT
t_{OESUD}	Data Setup Time for the Output Enable Register	J, H
t_{OEHD}	Data Hold Time for the Output Enable Register	J, H
t_{OESUE}	Enable Setup Time for the Output Enable Register	K, H
t_{OEHE}	Enable Hold Time for the Output Enable Register	K, H
$t_{OEPRE2Q}$	Asynchronous Preset-to-Q of the Output Enable Register	I, EOUT
$t_{OEREMPRE}$	Asynchronous Preset Removal Time for the Output Enable Register	I, H
$t_{OERECPRE}$	Asynchronous Preset Recovery Time for the Output Enable Register	I, H
t_{ICLKQ}	Clock-to-Q of the Input Data Register	A, E
t_{ISUD}	Data Setup Time for the Input Data Register	C, A
t_{IHD}	Data Hold Time for the Input Data Register	C, A
t_{ISUE}	Enable Setup Time for the Input Data Register	B, A
t_{IHE}	Enable Hold Time for the Input Data Register	B, A
t_{IPRE2Q}	Asynchronous Preset-to-Q of the Input Data Register	D, E
$t_{IREMPRE}$	Asynchronous Preset Removal Time for the Input Data Register	D, A
$t_{IRECPRE}$	Asynchronous Preset Recovery Time for the Input Data Register	D, A

*Note: *See Figure 2-25 on page 2-53 for more information.*

Fully Registered I/O Buffers with Synchronous Enable and Asynchronous Clear

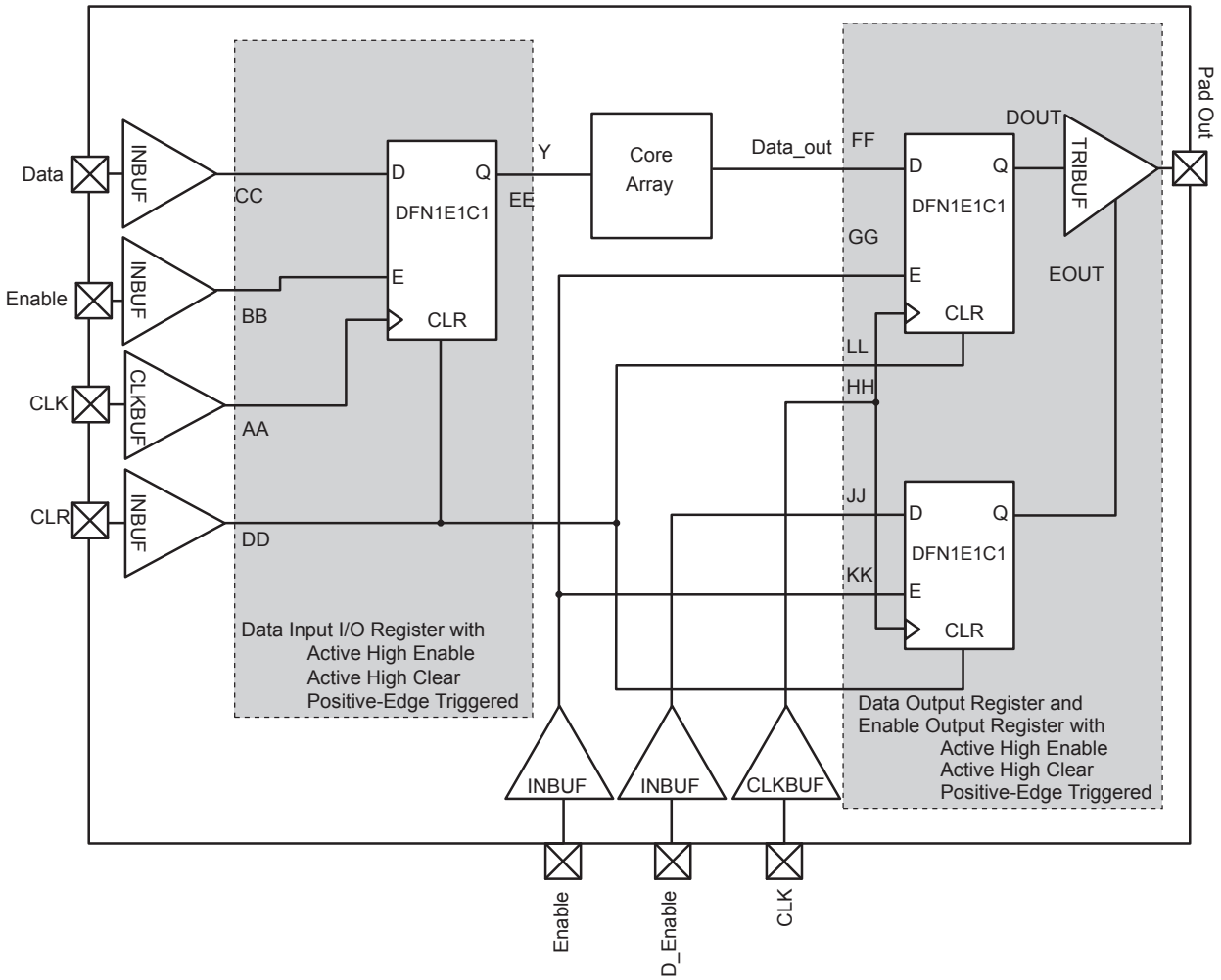


Figure 2-26 • **Timing Model of the Registered I/O Buffers with Synchronous Enable and Asynchronous Clear**

Timing Characteristics

Table 2-99 • RAM4K9
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V

Parameter	Description	–2	–1	Std.	Units
t_{AS}	Address setup time	0.25	0.28	0.33	ns
t_{AH}	Address hold time	0.00	0.00	0.00	ns
t_{ENS}	REN, WEN setup time	0.14	0.16	0.19	ns
t_{ENH}	REN, WEN hold time	0.10	0.11	0.13	ns
t_{BKS}	BLK setup time	0.23	0.27	0.31	ns
t_{BKH}	BLK hold time	0.02	0.02	0.02	ns
t_{DS}	Input data (DIN) setup time	0.18	0.21	0.25	ns
t_{DH}	Input data (DIN) hold time	0.00	0.00	0.00	ns
t_{CKQ1}	Clock High to new data valid on DOUT (output retained, WMODE = 0)	1.79	2.03	2.39	ns
	Clock High to new data valid on DOUT (flow-through, WMODE = 1)	2.36	2.68	3.15	ns
t_{CKQ2}	Clock High to new data valid on DOUT (pipelined)	0.89	1.02	1.20	ns
t_{C2CWWL} [1]	Address collision clk-to-clk delay for reliable write after write on same address—Applicable to Closing Edge	0.33	0.28	0.25	ns
t_{C2CWWH} [1]	Address collision clk-to-clk delay for reliable write after write on same address—Applicable to Rising Edge	0.30	0.26	0.23	ns
t_{C2CRWH} [1]	Address collision clk-to-clk delay for reliable read access after write on same address—Applicable to Opening Edge	0.45	0.38	0.34	ns
t_{C2CWRH} [1]	Address collision clk-to-clk delay for reliable write access after read on same address— Applicable to Opening Edge	0.49	0.42	0.37	ns
t_{RSTBQ}	RESET Low to data out Low on DO (flow-through)	0.92	1.05	1.23	ns
	RESET Low to Data Out Low on DO (pipelined)	0.92	1.05	1.23	ns
$t_{REMRSTB}$	RESET removal	0.29	0.33	0.38	ns
$t_{RECRSTB}$	RESET recovery	1.50	1.71	2.01	ns
$t_{MPWRSTB}$	RESET minimum pulse width	0.21	0.24	0.29	ns
t_{CYC}	Clock cycle time	3.23	3.68	4.32	ns
F_{MAX}	Maximum frequency	310	272	231	MHz

Notes:

1. *For more information, refer to the application note Simultaneous Read-Write Operations in Dual-Port SRAM for Flash-Based cSoCs and FPGAs.*
2. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-5 for derating values.*

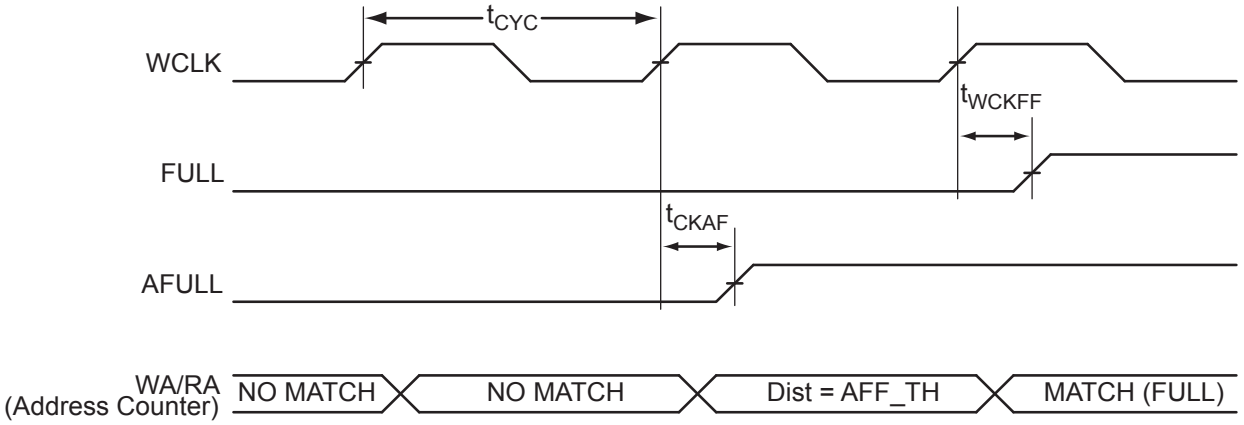


Figure 2-51 • **FIFO FULL Flag and AFULL Flag Assertion**

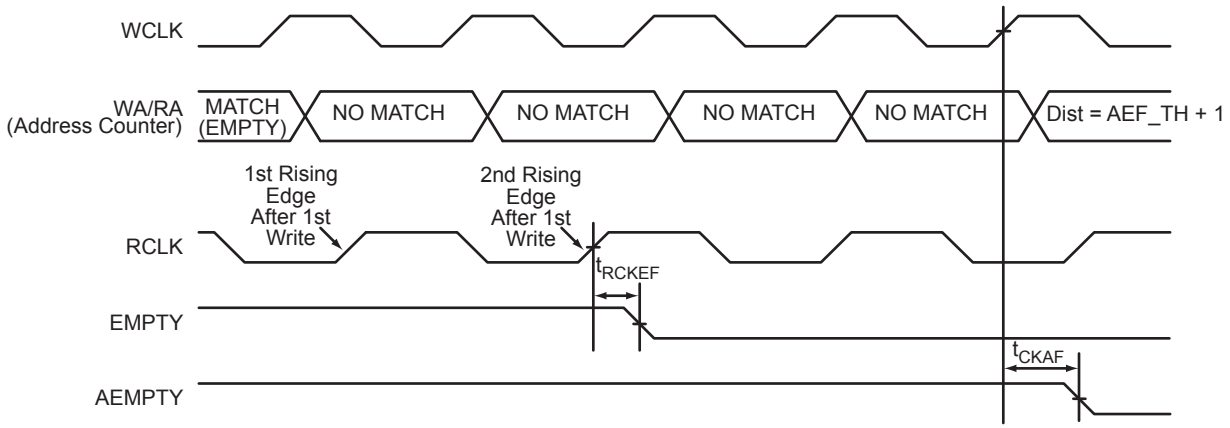


Figure 2-52 • **FIFO EMPTY Flag and AEMPTY Flag Deassertion**

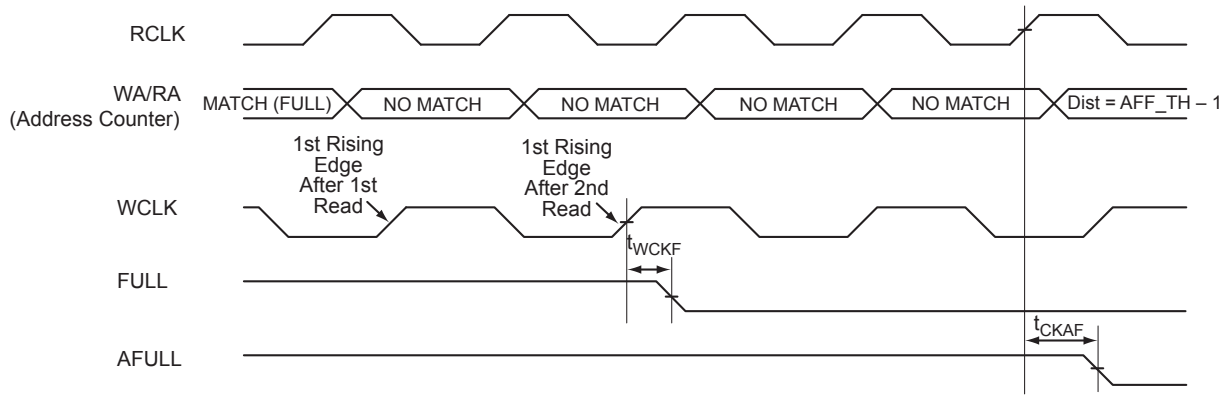


Figure 2-53 • **FIFO FULL Flag and AFULL Flag Deassertion**

PQ208	
Pin Number	**A3PE1500 Function**
109	TRST
110	VJTAG
111	VMV3
112	GDA0/IO110NPB3V2
113	GDB0/IO109NPB3V2
114	GDA1/IO110PPB3V2
115	GDB1/IO109PPB3V2
116	GDC0/IO108NDB3V2
117	GDC1/IO108PDB3V2
118	IO105NDB3V2
119	IO105PDB3V2
120	IO101NDB3V1
121	IO101PDB3V1
122	GND
123	VCCIB3
124	GCC2/IO90PSB3V0
125	GCB2/IO89PSB3V0
126	NC
127	IO88NDB3V0
128	GCA2/IO88PDB3V0
129	GCA1/IO87PPB3V0
130	GND
131	VCCPLC
132	GCA0/IO87NPB3V0
133	VCOMPLC
134	GCB0/IO86NDB2V3
135	GCB1/IO86PDB2V3
136	GCC1/IO85PSB2V3
137	IO83NDB2V3
138	IO83PDB2V3
139	IO81PSB2V3
140	VCCIB2
141	GND
142	VCC
143	IO73NDB2V2
144	IO73PDB2V2

PQ208	
Pin Number	**A3PE1500 Function**
145	IO71NDB2V2
146	IO71PDB2V2
147	IO67NDB2V1
148	IO67PDB2V1
149	IO65NDB2V1
150	IO65PDB2V1
151	GBC2/IO60PSB2V0
152	GBA2/IO58PSB2V0
153	GBB2/IO59PSB2V0
154	VMV2
155	GNDQ
156	GND
157	VMV1
158	GNDQ
159	GBA1/IO57PDB1V3
160	GBA0/IO57NDB1V3
161	GBB1/IO56PDB1V3
162	GND
163	GBB0/IO56NDB1V3
164	GBC1/IO55PDB1V3
165	GBC0/IO55NDB1V3
166	IO51PDB1V2
167	IO51NDB1V2
168	IO47PDB1V1
169	IO47NDB1V1
170	VCCIB1
171	VCC
172	IO43PSB1V1
173	IO41PDB1V1
174	IO41NDB1V1
175	IO35PDB1V0
176	IO35NDB1V0
177	IO31PDB0V3
178	GND
179	IO31NDB0V3
180	IO29PDB0V3

PQ208	
Pin Number	**A3PE1500 Function**
181	IO29NDB0V3
182	IO27PDB0V3
183	IO27NDB0V3
184	IO23PDB0V2
185	IO23NDB0V2
186	VCCIB0
187	VCC
188	IO18PDB0V2
189	IO18NDB0V2
190	IO15PDB0V1
191	IO15NDB0V1
192	IO12PSB0V1
193	IO11PDB0V1
194	IO11NDB0V1
195	GND
196	IO08PDB0V1
197	IO08NDB0V1
198	IO05PDB0V0
199	IO05NDB0V0
200	VCCIB0
201	GAC1/IO02PDB0V0
202	GAC0/IO02NDB0V0
203	GAB1/IO01PDB0V0
204	GAB0/IO01NDB0V0
205	GAA1/IO00PDB0V0
206	GAA0/IO00NDB0V0
207	GNDQ
208	VMV0

FG324	
Pin Number	**A3PE3000 FBGA**
N1	IO247NDB6V1
N2	IO247PDB6V1
N3	IO251NPB6V2
N4	GEC0/IO236NDB6V0
N5	VCOMPLE
N6	IO212NDB5V2
N7	IO212PDB5V2
N8	IO192NPB4V4
N9	IO174PDB4V2
N10	IO170PDB4V2
N11	GDA2/IO154PPB4V0
N12	GDB2/IO155PPB4V0
N13	GDA1/IO153PPB3V4
N14	VCOMPLD
N15	GDB0/IO152NDB3V4
N16	GDB1/IO152PDB3V4
N17	IO138NDB3V3
N18	IO138PDB3V3
P1	IO245PDB6V1
P2	GNDQ
P3	VMV6
P4	GEC1/IO236PDB6V0
P5	VCCPLE
P6	IO214PDB5V2
P7	VCCIB5
P8	GND
P9	IO174NDB4V2
P10	IO170NDB4V2
P11	GND
P12	VCCIB4
P13	IO155NPB4V0
P14	VCCPLD
P15	VJTAG
P16	GDC0/IO151NDB3V4
P17	GDC1/IO151PDB3V4
P18	IO142PDB3V3

FG324	
Pin Number	**A3PE3000 FBGA**
R1	IO245NDB6V1
R2	VCCIB6
R3	GEA1/IO234PPB6V0
R4	IO232NDB5V4
R5	GEB2/IO232PDB5V4
R6	IO214NDB5V2
R7	IO202PDB5V1
R8	IO194PDB5V0
R9	IO186PDB4V4
R10	IO178PDB4V3
R11	IO168NSB4V1
R12	IO164PDB4V1
R13	GDC2/IO156PDB4V0
R14	TCK
R15	VPUMP
R16	TRST
R17	VCCIB3
R18	IO142NDB3V3
T1	IO241PDB6V0
T2	GEA0/IO234NPB6V0
T3	IO233NPB5V4
T4	IO231NPB5V4
T5	VMV5
T6	IO208NDB5V1
T7	IO202NDB5V1
T8	IO194NDB5V0
T9	IO186NDB4V4
T10	IO178NDB4V3
T11	IO166NPB4V1
T12	IO164NDB4V1
T13	IO156NDB4V0
T14	VMV4
T15	TDI
T16	GNDQ
T17	TDO
T18	IO146PDB3V4

FG324	
Pin Number	**A3PE3000 FBGA**
U1	IO241NDB6V0
U2	GEA2/IO233PPB5V4
U3	GEC2/IO231PPB5V4
U4	VCCIB5
U5	GNDQ
U6	IO208PDB5V1
U7	IO198PPB5V0
U8	VCCIB5
U9	IO182NPB4V3
U10	IO180NPB4V3
U11	VCCIB4
U12	IO166PPB4V1
U13	IO162PDB4V1
U14	GNDQ
U15	VCCIB4
U16	TMS
U17	VMV3
U18	IO146NDB3V4
V1	GND
V2	IO218NDB5V3
V3	IO218PDB5V3
V4	IO206NDB5V1
V5	IO206PDB5V1
V6	IO198NPB5V0
V7	GND
V8	IO190NDB4V4
V9	IO190PDB4V4
V10	IO182PPB4V3
V11	IO180PPB4V3
V12	GND
V13	IO162NDB4V1
V14	IO160NDB4V0
V15	IO160PDB4V0
V16	IO158NDB4V0
V17	IO158PDB4V0
V18	GND

FG484	
Pin Number	**A3PE600 Function**
C21	NC
C22	VCCIB2
D1	NC
D2	NC
D3	NC
D4	GND
D5	GAA0/IO00NDB0V0
D6	GAA1/IO00PDB0V0
D7	GAB0/IO01NDB0V0
D8	IO05PDB0V0
D9	IO10PDB0V1
D10	IO12PDB0V2
D11	IO16NDB0V2
D12	IO23NDB1V0
D13	IO23PDB1V0
D14	IO28NDB1V1
D15	IO28PDB1V1
D16	GBB1/IO34PDB1V1
D17	GBA0/IO35NDB1V1
D18	GBA1/IO35PDB1V1
D19	GND
D20	NC
D21	NC
D22	NC
E1	NC
E2	NC
E3	GND
E4	GAB2/IO133PDB7V1
E5	GAA2/IO134PDB7V1
E6	GNDQ
E7	GAB1/IO01PDB0V0
E8	IO05NDB0V0
E9	IO10NDB0V1
E10	IO12NDB0V2
E11	IO16PDB0V2
E12	IO20NDB1V0

FG484	
Pin Number	**A3PE600 Function**
E13	IO24NDB1V0
E14	IO24PDB1V0
E15	GBC1/IO33PDB1V1
E16	GBB0/IO34NDB1V1
E17	GNDQ
E18	GBA2/IO36PDB2V0
E19	IO42NDB2V0
E20	GND
E21	NC
E22	NC
F1	NC
F2	IO131NDB7V1
F3	IO131PDB7V1
F4	IO133NDB7V1
F5	IO134NDB7V1
F6	VMV7
F7	VCCPLA
F8	GAC0/IO02NDB0V0
F9	GAC1/IO02PDB0V0
F10	IO15NDB0V2
F11	IO15PDB0V2
F12	IO20PDB1V0
F13	IO25NDB1V0
F14	IO27PDB1V0
F15	GBC0/IO33NDB1V1
F16	VCCPLB
F17	VMV2
F18	IO36NDB2V0
F19	IO42PDB2V0
F20	NC
F21	NC
F22	NC
G1	IO127NDB7V1
G2	IO127PDB7V1
G3	NC
G4	IO128PDB7V1

FG484	
Pin Number	**A3PE600 Function**
G5	IO129PDB7V1
G6	GAC2/IO132PDB7V1
G7	VCOMPLA
G8	GNDQ
G9	IO09NDB0V1
G10	IO09PDB0V1
G11	IO13PDB0V2
G12	IO21PDB1V0
G13	IO25PDB1V0
G14	IO27NDB1V0
G15	GNDQ
G16	VCOMPLB
G17	GBB2/IO37PDB2V0
G18	IO39PDB2V0
G19	IO39NDB2V0
G20	IO43PDB2V0
G21	IO43NDB2V0
G22	NC
H1	NC
H2	NC
H3	VCC
H4	IO128NDB7V1
H5	IO129NDB7V1
H6	IO132NDB7V1
H7	IO130PDB7V1
H8	VMV0
H9	VCCIB0
H10	VCCIB0
H11	IO13NDB0V2
H12	IO21NDB1V0
H13	VCCIB1
H14	VCCIB1
H15	VMV1
H16	GBC2/IO38PDB2V0
H17	IO37NDB2V0
H18	IO41NDB2V0

FG484	
Pin Number	**A3PE3000 Function**
C21	IO94PPB2V1
C22	VCCIB2
D1	IO293PDB7V2
D2	IO303NDB7V3
D3	IO305NDB7V3
D4	GND
D5	GAA0/IO00NDB0V0
D6	GAA1/IO00PDB0V0
D7	GAB0/IO01NDB0V0
D8	IO20PDB0V2
D9	IO22PDB0V2
D10	IO30PDB0V3
D11	IO38NDB0V4
D12	IO52NDB1V1
D13	IO52PDB1V1
D14	IO66NDB1V3
D15	IO66PDB1V3
D16	GBB1/IO80PDB1V4
D17	GBA0/IO81NDB1V4
D18	GBA1/IO81PDB1V4
D19	GND
D20	IO88PDB2V0
D21	IO90PDB2V1
D22	IO94NPB2V1
E1	IO293NDB7V2
E2	IO299PPB7V3
E3	GND
E4	GAB2/IO308PDB7V4
E5	GAA2/IO309PDB7V4
E6	GNDQ
E7	GAB1/IO01PDB0V0
E8	IO20NDB0V2
E9	IO22NDB0V2
E10	IO30NDB0V3
E11	IO38PDB0V4
E12	IO44NDB1V0

FG484	
Pin Number	**A3PE3000 Function**
E13	IO58NDB1V2
E14	IO58PDB1V2
E15	GBC1/IO79PDB1V4
E16	GBB0/IO80NDB1V4
E17	GNDQ
E18	GBA2/IO82PDB2V0
E19	IO86NDB2V0
E20	GND
E21	IO90NDB2V1
E22	IO98PDB2V2
F1	IO299NPB7V3
F2	IO301NDB7V3
F3	IO301PDB7V3
F4	IO308NDB7V4
F5	IO309NDB7V4
F6	VMV7
F7	VCCPLA
F8	GAC0/IO02NDB0V0
F9	GAC1/IO02PDB0V0
F10	IO32NDB0V3
F11	IO32PDB0V3
F12	IO44PDB1V0
F13	IO50NDB1V1
F14	IO60PDB1V2
F15	GBC0/IO79NDB1V4
F16	VCCPLB
F17	VMV2
F18	IO82NDB2V0
F19	IO86PDB2V0
F20	IO96PDB2V1
F21	IO96NDB2V1
F22	IO98NDB2V2
G1	IO289NDB7V1
G2	IO289PDB7V1
G3	IO291PPB7V2
G4	IO295PDB7V2

FG484	
Pin Number	**A3PE3000 Function**
G5	IO297PDB7V2
G6	GAC2/IO307PDB7V4
G7	VCOMPLA
G8	GNDQ
G9	IO26NDB0V3
G10	IO26PDB0V3
G11	IO36PDB0V4
G12	IO42PDB1V0
G13	IO50PDB1V1
G14	IO60NDB1V2
G15	GNDQ
G16	VCOMPLB
G17	GBB2/IO83PDB2V0
G18	IO92PDB2V1
G19	IO92NDB2V1
G20	IO102PDB2V2
G21	IO102NDB2V2
G22	IO105NDB2V2
H1	IO286PSB7V1
H2	IO291NPB7V2
H3	VCC
H4	IO295NDB7V2
H5	IO297NDB7V2
H6	IO307NDB7V4
H7	IO287PDB7V1
H8	VMV0
H9	VCCIB0
H10	VCCIB0
H11	IO36NDB0V4
H12	IO42NDB1V0
H13	VCCIB1
H14	VCCIB1
H15	VMV1
H16	GBC2/IO84PDB2V0
H17	IO83NDB2V0
H18	IO100NDB2V2

FG676	
Pin Number	A3PE1500 Function
G13	IO21NDB0V2
G14	IO27PDB0V3
G15	IO35NDB1V0
G16	IO39PDB1V0
G17	IO51NDB1V2
G18	IO53NDB1V2
G19	VCCIB1
G20	GBA2/IO58PPB2V0
G21	GNDQ
G22	IO64NDB2V1
G23	IO64PDB2V1
G24	IO72PDB2V2
G25	IO72NDB2V2
G26	IO78PDB2V2
H1	IO208NDB7V2
H2	IO208PDB7V2
H3	IO209NDB7V2
H4	IO209PDB7V2
H5	IO219NDB7V3
H6	GAC2/IO219PDB7V3
H7	VCCIB7
H8	VCC
H9	VCCIB0
H10	VCCIB0
H11	VCCIB0
H12	VCCIB0
H13	VCCIB0
H14	VCCIB1
H15	VCCIB1
H16	VCCIB1
H17	VCCIB1
H18	VCCIB1
H19	VCC
H20	VCC
H21	IO58NPB2V0
H22	IO70PDB2V1

FG676	
Pin Number	A3PE1500 Function
H23	IO69PDB2V1
H24	IO76PDB2V2
H25	IO76NDB2V2
H26	IO78NDB2V2
J1	IO197NDB7V0
J2	IO197PDB7V0
J3	VMV7
J4	IO215NDB7V3
J5	IO215PDB7V3
J6	IO214PDB7V3
J7	IO214NDB7V3
J8	VCCIB7
J9	VCC
J10	VCC
J11	VCC
J12	VCC
J13	VCC
J14	VCC
J15	VCC
J16	VCC
J17	VCC
J18	VCC
J19	VCCIB2
J20	IO62PDB2V0
J21	IO62NDB2V0
J22	IO70NDB2V1
J23	IO69NDB2V1
J24	VMV2
J25	IO80PDB2V3
J26	IO80NDB2V3
K1	IO195PDB7V0
K2	IO199NDB7V1
K3	IO199PDB7V1
K4	IO205NDB7V1
K5	IO205PDB7V1
K6	IO217PDB7V3

FG676	
Pin Number	A3PE1500 Function
K7	IO217NDB7V3
K8	VCCIB7
K9	VCC
K10	GND
K11	GND
K12	GND
K13	GND
K14	GND
K15	GND
K16	GND
K17	GND
K18	VCC
K19	VCCIB2
K20	IO65PDB2V1
K21	IO65NDB2V1
K22	IO74PDB2V2
K23	IO74NDB2V2
K24	IO75PDB2V2
K25	IO75NDB2V2
K26	IO84PDB2V3
L1	IO195NDB7V0
L2	IO198PPB7V0
L3	GNDQ
L4	IO201PDB7V1
L5	IO201NDB7V1
L6	IO210NDB7V2
L7	IO210PDB7V2
L8	VCCIB7
L9	VCC
L10	GND
L11	GND
L12	GND
L13	GND
L14	GND
L15	GND
L16	GND

FG896	
Pin Number	A3PE3000 Function
E17	IO49PDB1V1
E18	IO50PDB1V1
E19	IO58PDB1V2
E20	IO60NDB1V2
E21	IO77PDB1V4
E22	IO68NDB1V3
E23	IO68PDB1V3
E24	VCCIB1
E25	IO74PDB1V4
E26	VCC
E27	GBB1/IO80PPB1V4
E28	VCCIB2
E29	IO82NPB2V0
E30	GND
F1	IO296PPB7V2
F2	VCC
F3	IO306PDB7V4
F4	IO297PDB7V2
F5	VMV7
F6	GND
F7	GNDQ
F8	IO12NDB0V1
F9	IO12PDB0V1
F10	IO10PDB0V1
F11	IO16PDB0V1
F12	IO22NDB0V2
F13	IO30NDB0V3
F14	IO30PDB0V3
F15	IO36PDB0V4
F16	IO48NDB1V0
F17	IO48PDB1V0
F18	IO50NDB1V1
F19	IO58NDB1V2
F20	IO60PDB1V2
F21	IO77NDB1V4
F22	IO72NDB1V3

FG896	
Pin Number	A3PE3000 Function
F23	IO72PDB1V3
F24	GNDQ
F25	GND
F26	VMV2
F27	IO86PDB2V0
F28	IO92PDB2V1
F29	VCC
F30	IO100NPB2V2
G1	GND
G2	IO296NPB7V2
G3	IO306NDB7V4
G4	IO297NDB7V2
G5	VCCIB7
G6	GNDQ
G7	VCC
G8	VMV0
G9	VCCIB0
G10	IO10NDB0V1
G11	IO16NDB0V1
G12	IO22PDB0V2
G13	IO26PPB0V3
G14	IO38NPB0V4
G15	IO36NDB0V4
G16	IO46NDB1V0
G17	IO46PDB1V0
G18	IO56NDB1V1
G19	IO56PDB1V1
G20	IO66NDB1V3
G21	IO66PDB1V3
G22	VCCIB1
G23	VMV1
G24	VCC
G25	GNDQ
G26	VCCIB2
G27	IO86NDB2V0
G28	IO92NDB2V1

FG896	
Pin Number	A3PE3000 Function
G29	IO100PPB2V2
G30	GND
H1	IO294PDB7V2
H2	IO294NDB7V2
H3	IO300NDB7V3
H4	IO300PDB7V3
H5	IO295PDB7V2
H6	IO299PDB7V3
H7	VCOMPLA
H8	GND
H9	IO08NDB0V0
H10	IO08PDB0V0
H11	IO18PDB0V2
H12	IO26NPB0V3
H13	IO28NDB0V3
H14	IO28PDB0V3
H15	IO38PPB0V4
H16	IO42NDB1V0
H17	IO52NDB1V1
H18	IO52PDB1V1
H19	IO62NDB1V2
H20	IO62PDB1V2
H21	IO70NDB1V3
H22	IO70PDB1V3
H23	GND
H24	VCOMPLB
H25	GBC2/IO84PDB2V0
H26	IO84NDB2V0
H27	IO96PDB2V1
H28	IO96NDB2V1
H29	IO89PDB2V0
H30	IO89NDB2V0
J1	IO290NDB7V2
J2	IO290PDB7V2
J3	IO302NDB7V3
J4	IO302PDB7V3

Revision	Changes	Page
v2.1 (continued)	The words "ambient temperature" were added to the temperature range in the "Temperature Grade Offerings", "Speed Grade and Temperature Grade Matrix", and "Speed Grade and Temperature Grade Matrix" sections.	1-I
	The "Clock Conditioning Circuit (CCC) and PLL" section was updated.	1-I
	The caption "Main (chip)" in Figure 2-9 • Overview of Automotive ProASIC3 VersaNet Global Network was changed to "Chip (main)."	2-9
	The T_J parameter in Table 3-2 • Recommended Operating Conditions was changed to T_A, ambient temperature, and table notes 4–6 were added.	3-2
	The "PLL Macro" section was updated to add information on the VCO and PLL outputs during power-up.	2-15
v2.0 (April 2007)	In the "Temperature Grade Offerings" section, Ambient was deleted.	iii
	Ambient was deleted from "Temperature Grade Offerings".	iii
	Ambient was deleted from the "Speed Grade and Temperature Grade Matrix".	iv
	The "PLL Macro" section was updated to include power-up information.	2-15
	Table 2-13 • ProASIC3E CCC/PLL Specification was updated.	2-30
	Figure 2-19 • Peak-to-Peak Jitter Definition is new.	2-18
	The "SRAM and FIFO" section was updated with operation and timing requirement information.	2-21
	The "RESET" section was updated with read and write information.	2-25
	The "RESET" section was updated with read and write information.	2-25
	The "Introduction" in the "Advanced I/Os" section was updated to include information on input and output buffers being disabled.	2-28
	In the Table 2-15 • Levels of Hot-Swap Support, the ProASIC3 compliance descriptions were updated for levels 3 and 4.	2-34
	Table 2-45 • I/O Hot-Swap and 5 V Input Tolerance Capabilities in ProASIC3E Devices was updated.	2-64
	Notes 3, 4, and 5 were added to Table 2-17 • Comparison Table for 5 V–Compliant Receiver Scheme. 5 x 52.72 was changed to 52.7 and the Maximum current was updated from 4 x 52.7 to 5 x 52.7.	2-40
	The "VCCPLF PLL Supply Voltage" section was updated.	2-50
	The "VPUMP Programming Supply Voltage" section was updated.	2-50
	The "GL Globals" section was updated to include information about direct input into quadrant clocks.	2-51
	VJTAG was deleted from the "TCK Test Clock" section.	2-51
	In Table 2-22 • Recommended Tie-Off Values for the TCK and TRST Pins, TSK was changed to TCK in note 2. Note 3 was also updated.	2-51
	Ambient was deleted from Table 3-2 • Recommended Operating Conditions. VPUMP programming mode was changed from "3.0 to 3.6" to "3.15 to 3.45".	3-2
	Note 3 is new in Table 3-4 • Overshoot and Undershoot Limits (as measured on quiet I/Os).	3-2
	In EQ 3-2, 150 was changed to 110 and the result changed to 5.88.	3-5